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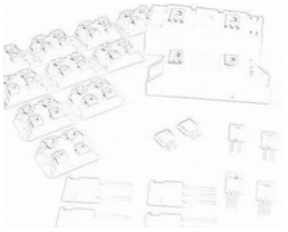

The Low V_F Schottkys for “80 to 90 PLUS” Applications

Monday, 19 November 2007

Sirectifier Global Corp. (SGC) announced that the Low Forward Voltage Drop (V_F) Schottkys including various barriers for “80 to 90 PLUS” applications of CEC in the U.S.A. The Low V_F Schottkys indeed reduced the conduction loss on the switching-mode power supply (SMPS) and then make the efficiency of SMPS higher and higher. The packages of the Low V_F Schottkys are including TO-220 and TO-247 from 30A to 40A for all kinds of power design for example Fly-back, Half-bridge and Forward topologies.

The following information is the normal data of the Low V_F Schottkys. For further details, please contact SGC at the location nearest you.

NO	P/N	I_F (A)	V_B (V)	V_F (V)		I_R (mA)	Tj(max)	Barrier
				@25˚ C	@125˚ C	@25˚ C		
1	SBL3030CT/PT	30	30	0.48	0.35	1.0	150˚ C	Alloy
2	SBL30L30CT/PT	30	30	0.45	0.32	1.0	150˚ C	Alloy
3	SBL30L45CT/PT	30	45	0.52	0.41	1.0	150˚ C	Mo
4	SBL30LL60CT/PT	30	60	0.52	0.38	1.0	150˚ C	Mo
5	SBL30L60CT/PT	30	60	0.6	0.45	1.0	150˚ C	Mo
6	MBR30L100CT/PT	30	100	0.72	0.60	0.01	175˚ C	Pt
7	SBL4030CT/PT	40	30	0.48	0.35	1.0	150˚ C	Alloy
8	SBL40L45CT/PT	40	45	0.52	0.41	1.0	150˚ C	Mo
9	SBL4060CT/PT	40	60	0.65	0.50	1.0	150˚ C	Mo
10	SBL40L60CT/PT	40	60	0.6	0.45	1.0	150˚ C	Mo
11	MBR40L100CT/PT	40	100	0.75	0.62	0.01	175˚ C	Pt

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